

isc Silicon PNP Darlington Power Transistor

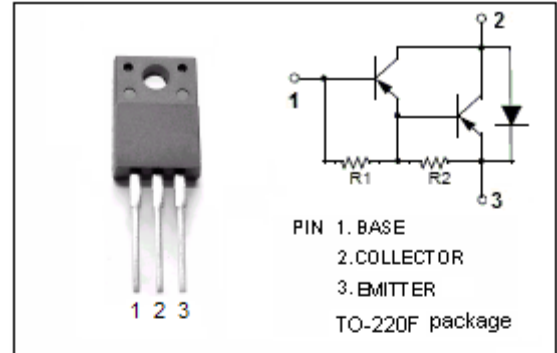
2SB1495

DESCRIPTION

- High DC Current Gain-
: $h_{FE} = 2000(\text{Min}) @ (V_{CE} = -2V, I_C = -2A)$
- Low-Collector Saturation Voltage-
: $V_{CE(\text{sat})} = -1.5V(\text{Max.}) @ I_C = -1.5A$
- Complement to Type 2SD2257

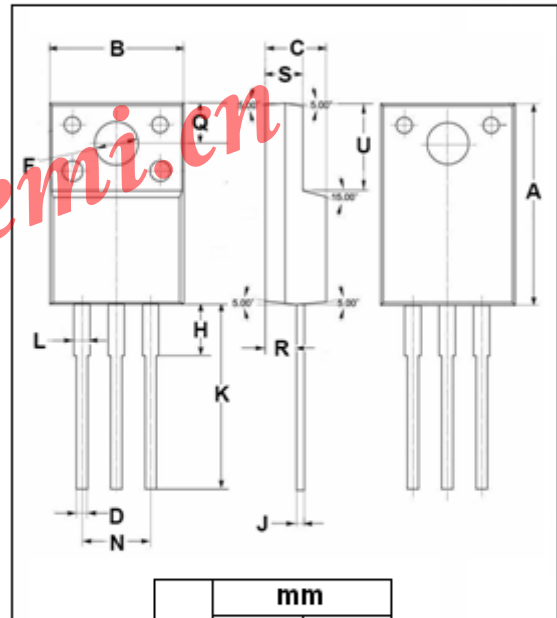
APPLICATIONS

- Designed for high power switching applications.



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-8	V
I_C	Collector Current-Continuous	-3	A
I_{CM}	Collector Current-Pulse	-5	A
I_B	Base Current-Continuous	-0.3	A
P_C	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	2	W
	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	20	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



DIM	mm	
	MIN	MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.80
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.85
U	6.40	6.60

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ELECTRICAL CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -10mA; I _B = 0	-100			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -1.5A; I _B = -1.5mA			-1.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = -1.5A; I _B = -1.5mA			-2.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -100V; I _E = 0			-10	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -8V; I _C = 0			-4.0	mA
h _{FE-1}	DC Current Gain	I _C = -1A; V _{CE} = -2V	2000			
h _{FE-2}	DC Current Gain	I _C = -2A; V _{CE} = -2V	2000			

Switching Times

t _{on}	Turn-on Time	I _C = -1.5A, I _{B1} = -I _{B2} = -1.5mA, V _{CC} ≈ -30V; R _L = 20 Ω		0.5		μ s
t _{stg}	Storage Time			1.0		μ s
t _f	Fall Time			0.4		μ s